



Micro Commercial Components
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2SD845

Features

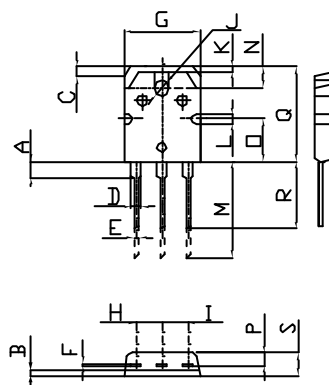
- With TO-3P(I) package
- Recommended for 60~80W high-fidelity frequency amplifier output stage

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	150	V
V_{CBO}	Collector-Base Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current	12	A
P_C	Collector power dissipation	120	W
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

NPN Silicon Power Transistors

TO-3P(I)



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=50\text{mA}$, $I_B=0$)	150	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=150\text{Vdc}$, $I_E=0$)	---	50	μA
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=5.0\text{Vdc}$, $I_C=0$)	---	50	μA

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer ratio ($I_C=1.0\text{A}$, $V_{CE}=5.0\text{Vdc}$)	100	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=5.0\text{A}$, $I_B=0.5\text{A}$)	---	2.0	Vdc

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	.130	---	3.30	
B	---	.071	---	1.80	
C	.079		2.00		
D	.067	.091	1.70	2.30	
E	.030	.051	.75	1.30	
F	.012	.028	.30	.70	
G	---	.626	---	15.90	
H	.205	.220	5.20	5.60	
I	.207	.222	5.25	5.65	
J	.118	.134	3.00	3.40	Ø
K	.039		1.00		
L	.079		2.00		
M	.748	.827	19.00	21.00	
N	.177		4.50		
O	.354		9.00		
P	.110		2.80		
Q	.067	.091	1.70	2.30	
R	.512	.551	13.00	14.00	
S	---	.189	---	4.80	